

RELIABILITY REPORT
FOR
DS28E07+T
PLASTIC ENCAPSULATED DEVICES

December 6, 2016

MAXIM INTEGRATED

160 RIO ROBLES
SAN JOSE, CA 95134

Approved by
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Conclusion

The DS28E07+T successfully meets the quality and reliability standards required of all Maxim Integrated products. In addition, Maxim Integrated's continuous reliability monitoring program ensures that all outgoing product will continue to meet Maxim Integrated's quality and reliability standards.

Table of Contents

I.Device Description	IV.Die Information
II.Manufacturing Information	V.Quality Assurance Information
III.Packaging Information	VI.Reliability Evaluation
.....Attachments	

I. Device Description

A. General

The DS28E07 is a 1024-bit, 1-Wire® EEPROM chip organized as four memory pages of 256 bits each. Data is written to an 8-byte scratchpad, verified, and then copied to the EEPROM memory. As a special feature, the four user memory pages can individually be write protected or put in EPROM-emulation mode, where bits can only be changed from a 1 to a 0 state. Each device has its own guaranteed unique 64-bit ROM identification number (ROM ID) that is factory programmed into the chip. The communication follows the 1-Wire protocol with the ROM ID acting as node address in the case of a multiple-device 1-Wire network.

II. Manufacturing Information

A. Description/Function:	1024-Bit, 1-Wire EEPROM
B. Process:	GS18
C. Fabrication Location:	USA
D. Assembly Location:	Philippines
E. Date of Initial Production:	September 25, 2015

III. Packaging Information

A. Package Type:	3-pin TSOC
B. Lead Frame:	Copper
C. Lead Finish:	100% Matte Tin
D. Die Attach:	Conductive
E. Bondwire:	Au (1 mil dia.)
F. Mold Material:	Epoxy with silica filler
G. Assembly Diagram:	#05-0637
H. Flammability Rating:	Class UL94-V0
I. Single Layer Theta Ja:	160°C/W
J. Single Layer Theta Jc:	4°C/W
K. Multi Layer Theta Ja:	131.9°C/W
L. Multi Layer Theta Jc:	4°C/W

IV. Quality Assurance Information

A. Quality Assurance Contacts:	Eric Wright (Reliability Engineering) Bryan Preeshl (Vice President of QA)
B. Outgoing Inspection Level:	0.1% for all electrical parameters guaranteed by the Datasheet. 0.1% for all Visual Defects.
C. Observed Outgoing Defect Rate:	< 50 ppm
D. Sampling Plan:	Mil-Std-105D

V. Reliability Evaluation

A. Accelerated Life Test

The results of the 135C biased (static) life test are shown in Table 1. Using these results, the Failure Rate (λ) is calculated as follows:

$$\lambda = \frac{1}{\text{MTTF}} = \frac{1.83}{192 \times 4340 \times 160 \times 2} \quad (\text{Chi square value for MTTF upper limit})$$

(where 4340 = Temperature Acceleration factor assuming an activation energy of 0.8eV)

$$\lambda = 6.87 \times 10^{-9}$$

$$\lambda = 6.87 \text{ F.I.T. (60\% confidence level @ 25°C)}$$

B. E.S.D. and Latch-Up Testing

The ES02-0 die type has been found to have all pins able to withstand a transient pulse of:

ESD-HBM: +/- 2500V per JEDEC JESD22-A114

ESD-CDM: +/- 750V per JEDEC JESD22-C101

Latch-Up testing has shown that this device withstands overvoltage testing (1.5Vcc) per JEDEC JESD78.

Table 1
Reliability Evaluation Test Results

DS28E07+T

TEST ITEM	TEST CONDITION	FAILURE IDENTIFICATION	SAMPLE SIZE	NUMBER OF FAILURES	COMMENTS
Static Life Test (Note 1)	Ta = 135C Biased Time = 192 hrs.	DC Parameters & functionality	160	0	

Note 1: Life Test Data may represent plastic DIP qualification lots.